

DFM600LXS12-A000

Fast Recovery Diode Module

Preliminary Information

DS5477-1.2 July 2001

FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Voltage Drop
- Isolated Base

APPLICATIONS

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Snubber Circuits
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM600LXS12-A000 is a single 1200 volt, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation making the device suitable for the latest drive designs employing pwm and high frequency switching.

These modules incorporate electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM600LXS12-A000

Note: When ordering, please use the complete part number.

KEY PARAMETERS

V_{RRM}		1200V
V _E	(typ)	1.9V
اً	(max)	600A
I _{FM}	(max)	1200A

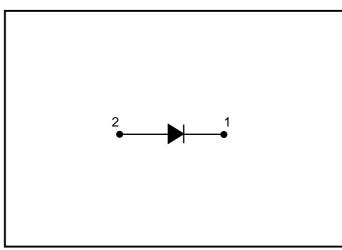


Fig. 1 Circuit diagram

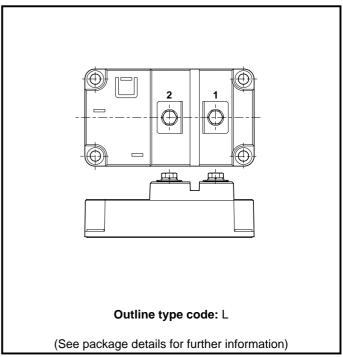


Fig. 2 Electrical connections - (not to scale)



ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{RRM}	Repetitive peak reverse voltage	T _{vj} = 125°C	1200	V
I _F	Forward current (per arm)	DC, T _{case} = 65°C	600	А
I _{FM}	Max. forward current	$T_{case} = 110^{\circ}C, t_{p} = 1 ms$	1200	А
l²t	I²t value fuse current rating	$V_R = 0, t_p = 10 \text{ms}, T_{vj} = 125^{\circ}\text{C}$	100	kA ² s
Pmax	Maximum power dissipation	T _{case} = 25°C, T _{vj} = 125°C	2080	W
V_{isol}	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4	kV
Q_{pd}	Partial discharge	IEC1287. V ₁ = 1200V, V ₂ = 900V, 50Hz RMS	10	рС

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
R _{th(j-c)}	Thermal resistance - diode (per arm)	Continuous dissipation -	-	-	48	°C/kW
		junction to case				
R _{th(c-h)}	Thermal resistance - case to heatsink	Mounting torque 5Nm	-	-	15	°C/kW
	(per module)	(with mounting grease)				
T _j	Junction temperature	-	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
-	Screw torque	Mounting - M5	-	-	5	Nm
		Electrical connections - M5	-	-	5	Nm



STATIC ELECTRICAL CHARACTERISTICS

 T_{vi} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
I _{RM}	Peak reverse current	V _R = 1200V, T _{vj} = 125°C	-	-	10	mA
V _F	Forward voltage	I _F = 600A	-	1.9	2.2	V
		I _F = 600A, T _{vj} = 125°C	-	2.1	2.4	V
L	Inductance	-	-	15	-	nH

DYNAMIC ELECTRICAL CHARACTERISTICS

 $T_{vj} = 25$ °C unless stated otherwise.

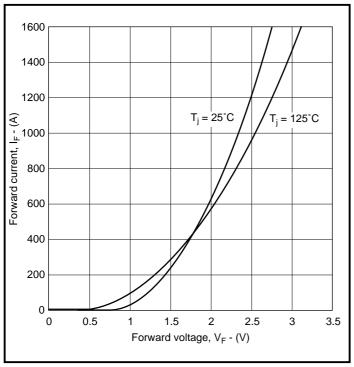
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
I _{rr}	Reverse recovery current	I _F = 600A,	-	400	-	Α
Q _{rr}	Reverse recovery charge	dl _F /dt = 4500A/μs,	-	100	-	μС
E _{rec}	Reverse recovery energy	V _R = 600V	-	40	-	mJ

T_{v_j} = 125°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
I _{rr}	Reverse recovery current	I _F = 600A,	-	475	-	А
Q _{rr}	Reverse recovery charge	dl _F /dt = 4200A/μs,	-	150	-	μС
E _{rec}	Reverse recovery energy	V _R = 600V	-	70	-	mJ



TYPICAL CHARACTERISTICS



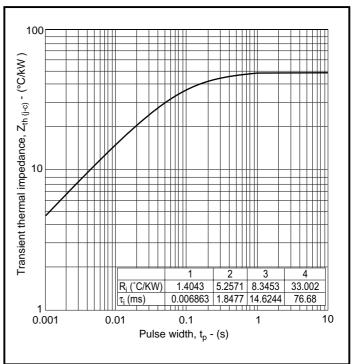


Fig. 2 Diode typical forward characteristics



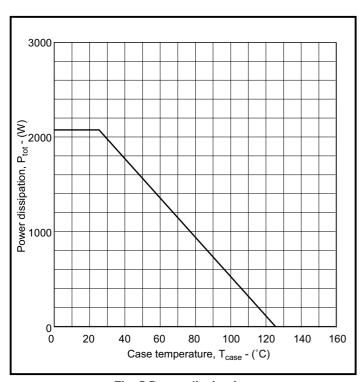


Fig. 5 Power dissipation

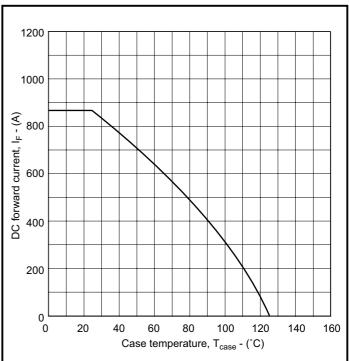


Fig. 6DC current rating vs case temperature



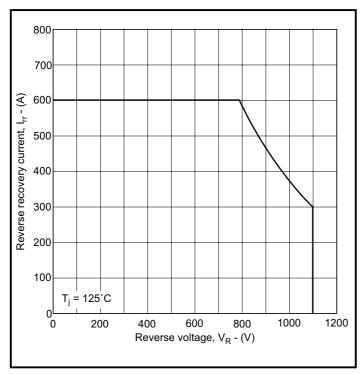
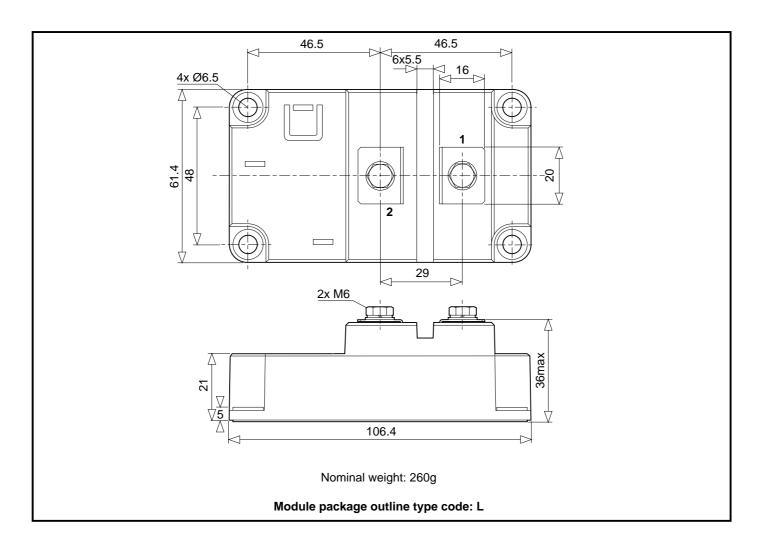


Fig. 7 RBSOA



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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